

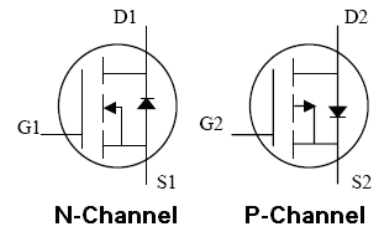
Features

- N+P Channel
- Enhancement mode
- Low on-resistance $R_{DS(on)}$ @ $V_{GS}=\pm 4.5V$
- Fast Switching
- Pb-free lead plating; RoHS compliant



Part ID	Package Type	Marking	Tape and reel information
VSO025C03MC	SOP8	025C03MC	3000pcs/Reel

V_{DS}	30	-30	V
$R_{DS(on),TYP} @ V_{GS}=\pm 10V$	15	23	m Ω
$R_{DS(on),TYP} @ V_{GS}=\pm 4.5V$	23	38	m Ω
I_D	10	-8	A

SOP8


Maximum ratings, at $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating		Unit	
		NMOS	PMOS		
$V_{(BR)DSS}$	Drain-Source breakdown voltage	30	-30	V	
I_S	Diode continuous forward current	$T_A = 25^\circ\text{C}$	1.6	-1.6	A
I_D	Continuous drain current @ $V_{GS}=\pm 10V$	$T_A = 25^\circ\text{C}$	10	-8	A
		$T_A = 100^\circ\text{C}$	6	-5	A
I_{DM}	Pulse drain current tested ①	$T_A = 25^\circ\text{C}$	40	-32	A
EAS	Avalanche energy, single pulsed ②		14	33	mJ
P_D	Maximum power dissipation	$T_A = 25^\circ\text{C}$	2	2	W
V_{GS}	Gate-Source voltage		± 20	± 20	V
MSL			Level 3		
$T_{STG} T_J$	Storage and operating temperature range		-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C/W}$

N-Channel Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =30V,V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =30V,V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250μA	1.3	1.9	2.4	V
R _{DS(ON)}	Drain-Source On-State Resistance ③	V _{GS} =10V, I _D =8A	--	15	19	mΩ
		V _{GS} =4.5V, I _D =4A	--	23	29	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =15V,V _{GS} =0V, f=1MHz	350	460	550	pF
C _{oss}	Output Capacitance		75	130	pF	
C _{rss}	Reverse Transfer Capacitance		60	110	pF	
R _g	Gate Resistance	f=1MHz	--	4.8	--	Ω
Q _g	Total Gate Charge	V _{DS} =15V,I _D =8A, V _{GS} =10V	--	11.3	--	nC
Q _{gs}	Gate Source Charge		--	3	--	nC
Q _{gd}	Gate Drain Charge		--	4.3	--	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =15V, I _D =8A, R _G =3Ω, V _{GS} =10V	--	7	--	nS
t _r	Turn on Rise Time		--	10	--	nS
t _{d(off)}	Turn Off Delay Time		-	22	--	nS
t _f	Turn Off Fall Time		--	7	--	nS
Source Drain Diode Characteristics						
V _{SD}	Forward on voltage	I _{SD} =8A,V _{GS} =0V	--	0.9	1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C,I _{sd} =8A, V _{GS} =0V	--	9.5	--	nS
Q _{rr}	Reverse Recovery Charge	di/dt=500A/μs	--	11.8	--	nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 6A, V_{GS} =10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle≤ 2%.

P-Channel Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =-30V, V _{GS} =0V	--	--	-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.3	-1.9	-2.4	V
R _{DS(ON)}	Drain-Source On-State Resistance ③	V _{GS} =-10V, I _D =-8A	--	23	29	mΩ
		V _{GS} =-4.5V, I _D =-4A	--	38	47	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	760	860	960	pF
C _{oss}	Output Capacitance		60	140	200	pF
C _{rss}	Reverse Transfer Capacitance		30	95	150	pF
R _g	Gate Resistance	f=1MHz	--	10.6	--	Ω
Q _g	Total Gate Charge	V _{DS} =-15V, I _D =-8A, V _{GS} =-10V	--	19	--	nC
Q _{gs}	Gate Source Charge		--	4.3	--	nC
Q _{gd}	Gate Drain Charge		--	6.5	--	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =-15V, I _D =-8A, R _G =3Ω, V _{GS} =-10V	--	6	--	ns
t _r	Turn on Rise Time		--	5	--	ns
t _{d(off)}	Turn Off Delay Time		-	25	--	ns
t _f	Turn Off Fall Time		--	7	--	ns
Source Drain Diode Characteristics						
V _{SD}	Forward on voltage	I _{SD} =-8A, V _{GS} =0V	--	-0.9	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C, I _{sd} =-8A, V _{GS} =0V	--	7	--	nS
Q _{rr}	Reverse Recovery Charge	di/dt=-500A/μs	--	6.3	--	nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH, R_G = 25Ω, I_{AS} = -9A, V_{GS} = -10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

N-Channel Typical Characteristics

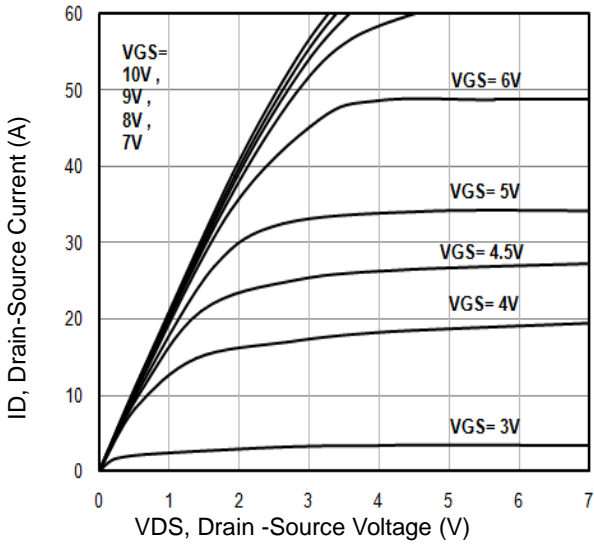


Fig1. Typical Output Characteristics

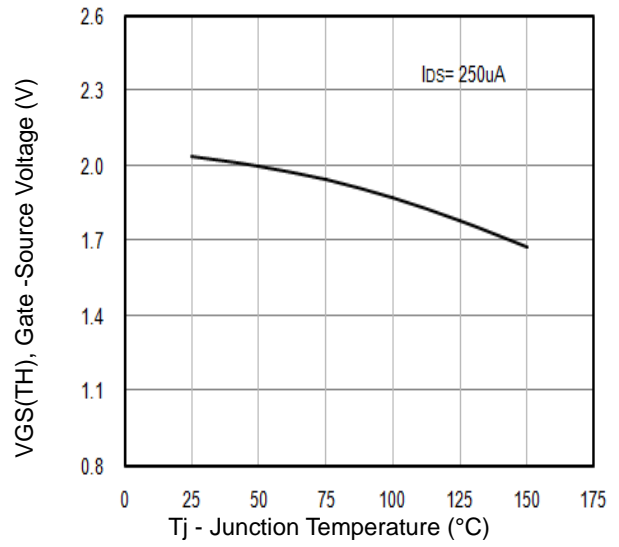


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

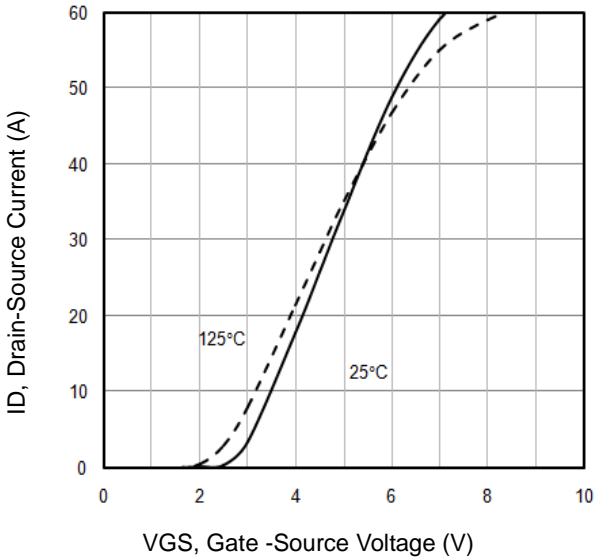


Fig3. Typical Transfer Characteristics

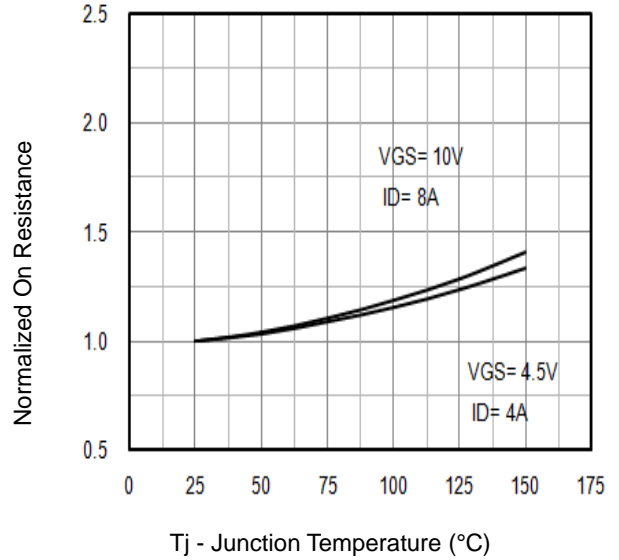


Fig4. Normalized On-Resistance Vs. T_j

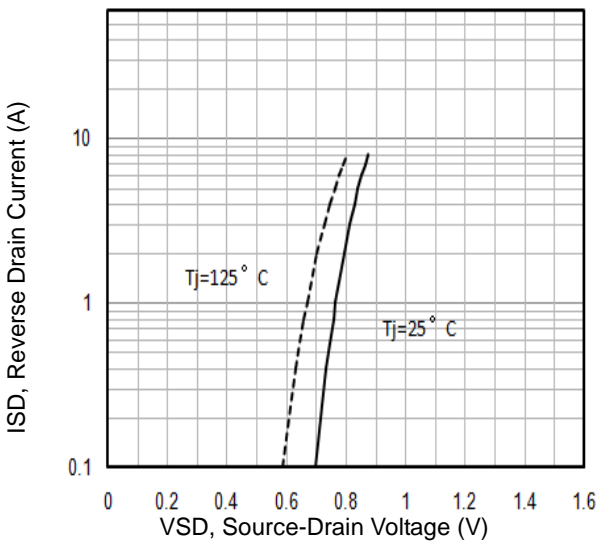


Fig5. Typical Source-Drain Diode Forward Voltage

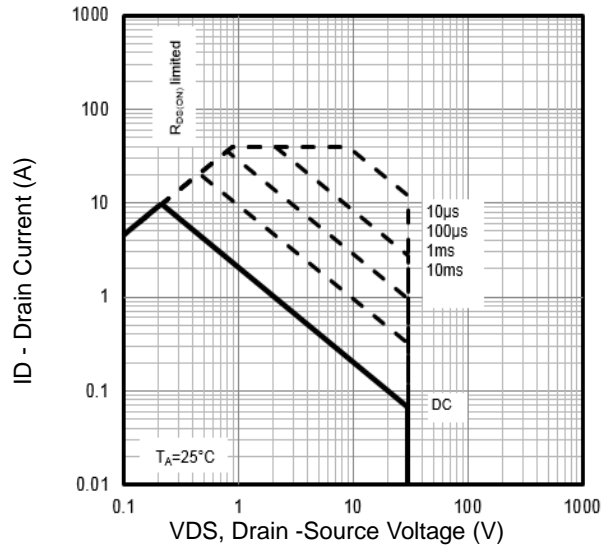


Fig6. Maximum Safe Operating Area

N-Channel Typical Characteristics

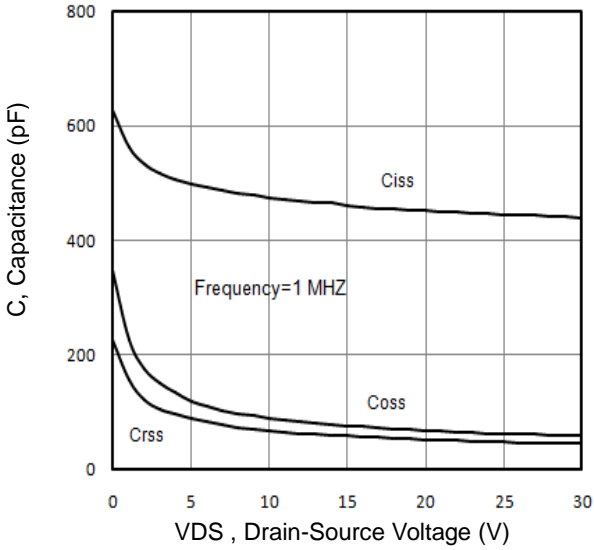


Fig7. Typical Capacitance Vs.Drain-Source Voltage

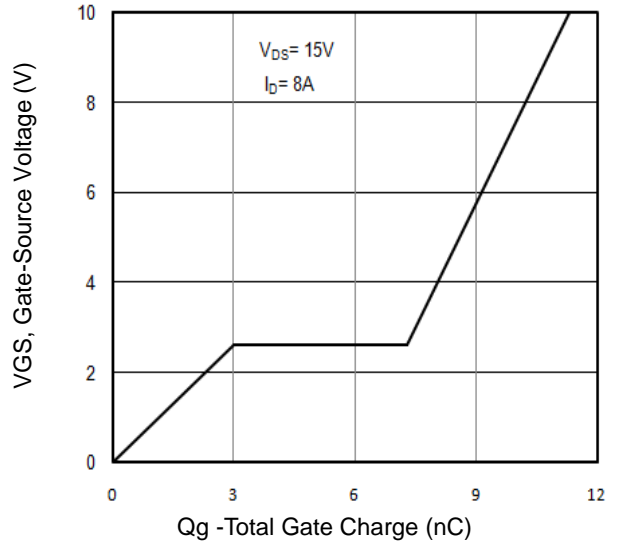


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

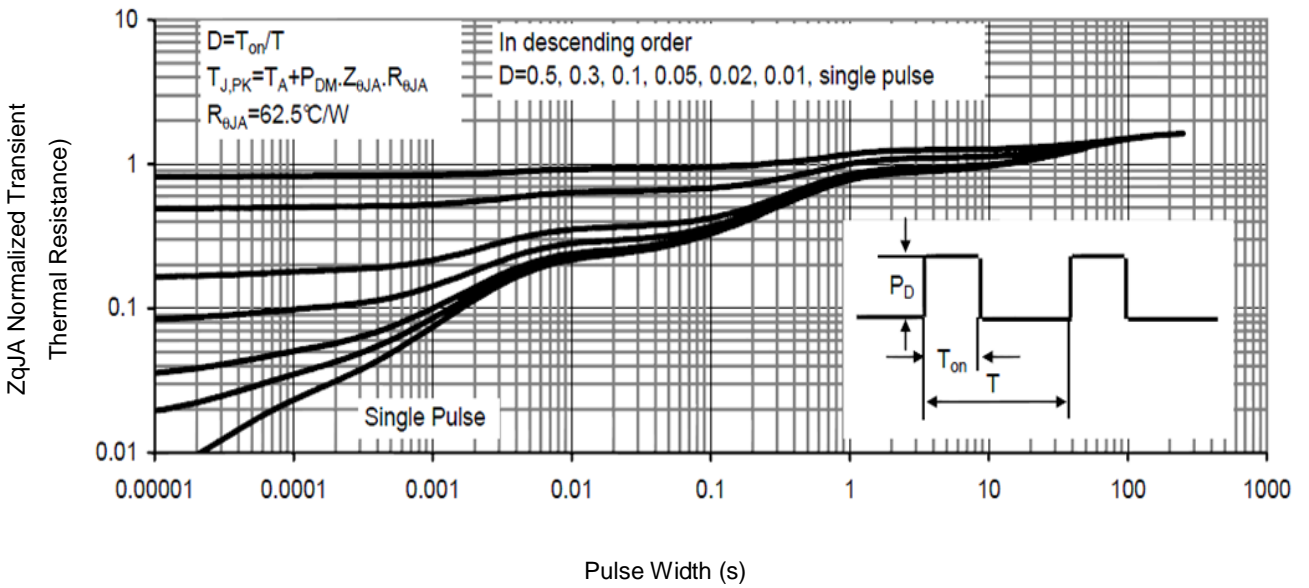


Fig 9 .Normalized Maximum Transient Thermal Impedance

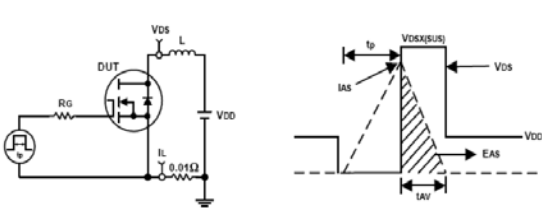


Fig10. Unclamped Inductive Test Circuit and waveforms

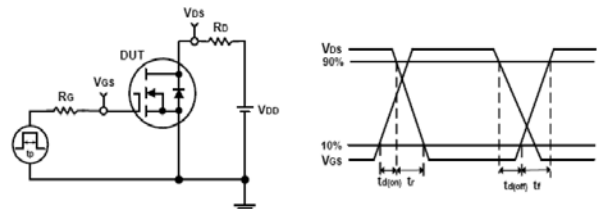


Fig11. Switching Time Test Circuit and waveforms

P-Channel Typical Characteristics

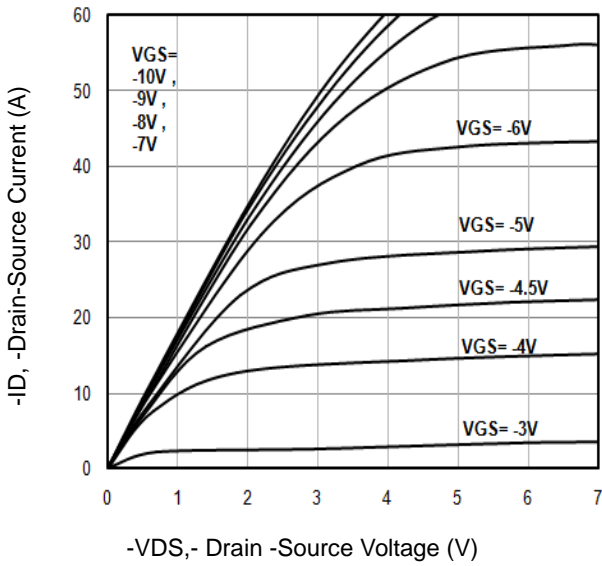


Fig1. Typical Output Characteristics

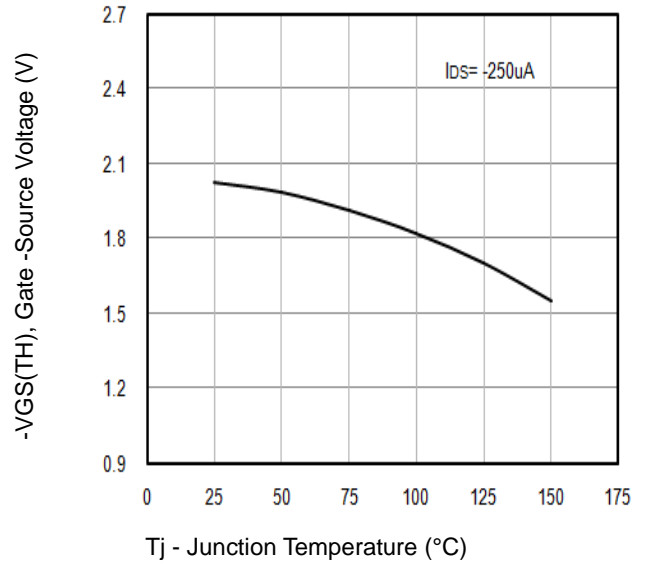


Fig2. $-V_{GS(TH)}$ Gate -Source Voltage Vs. T_j

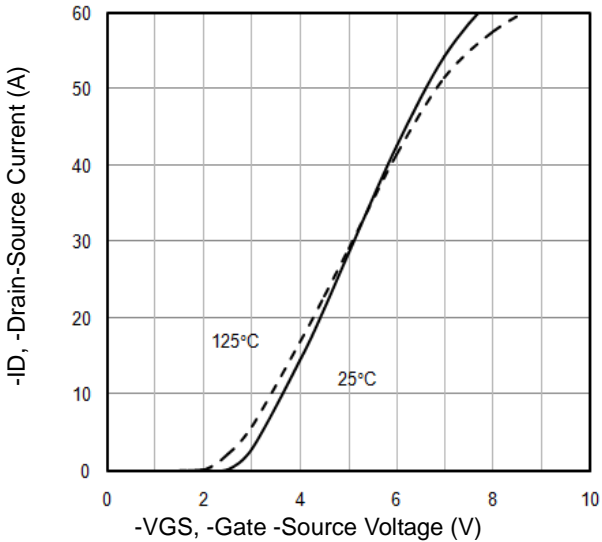


Fig3. Typical Transfer Characteristics

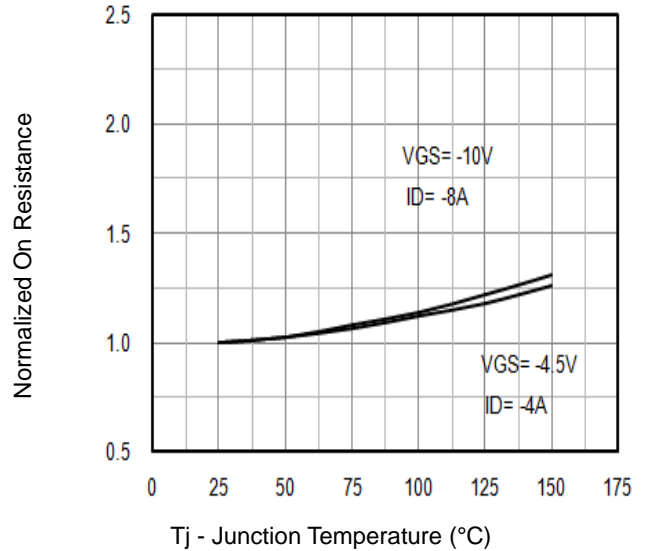


Fig4. Normalized On-Resistance Vs. T_j

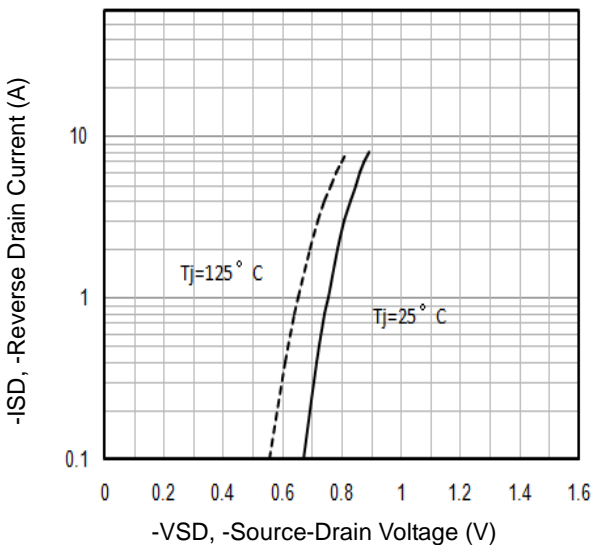


Fig5. Typical Source-Drain Diode Forward Voltage

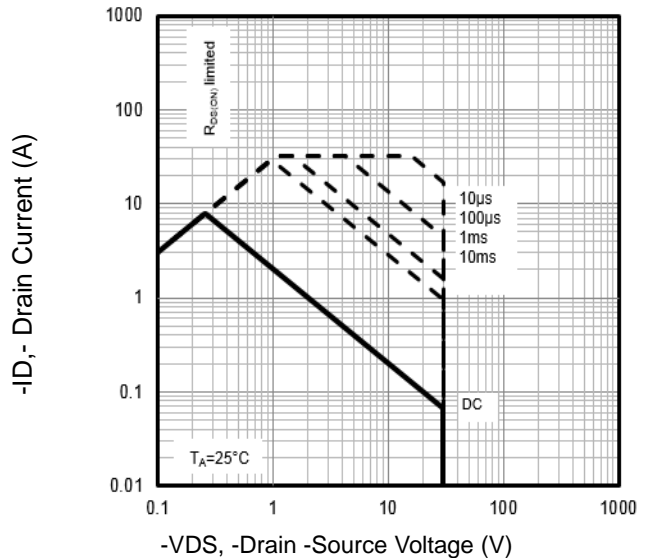


Fig6. Maximum Safe Operating Area

P-Channel Typical Characteristics

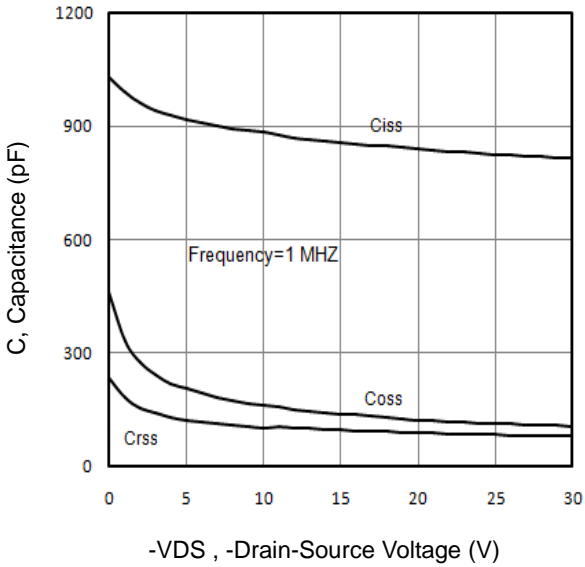


Fig7. Typical Capacitance Vs.Drain-Source Voltage

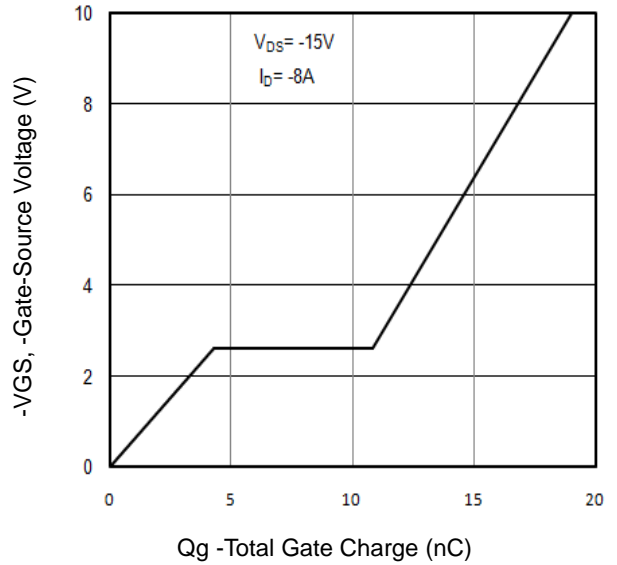


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

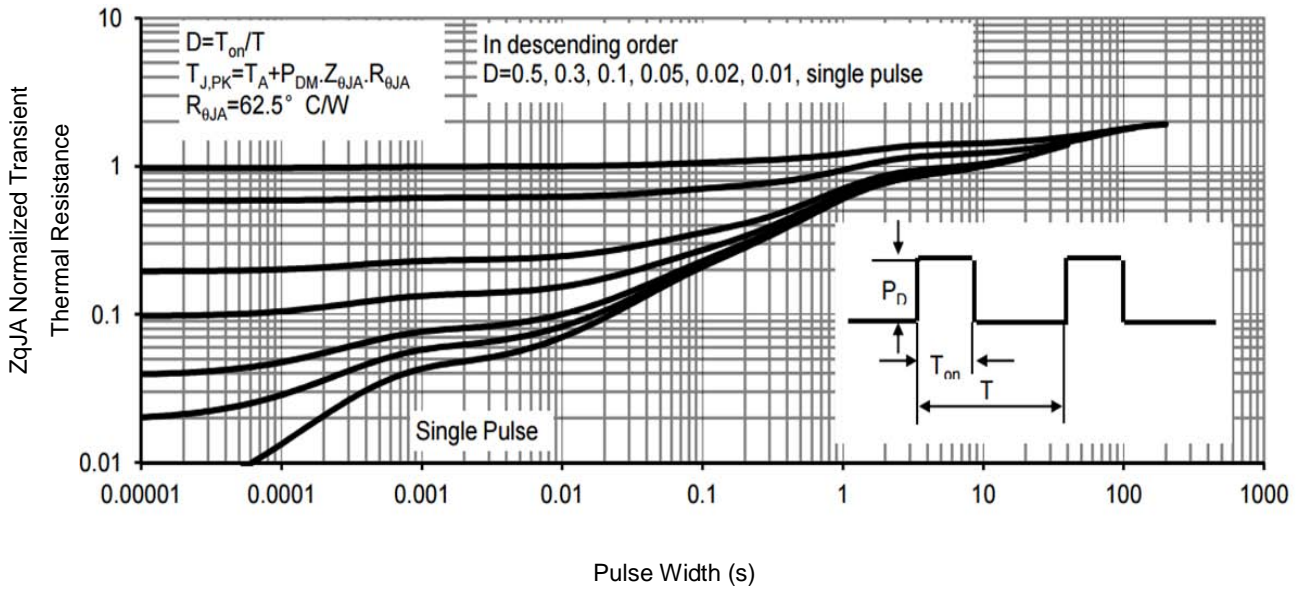


Fig9. Normalized Maximum Transient Thermal Impedance

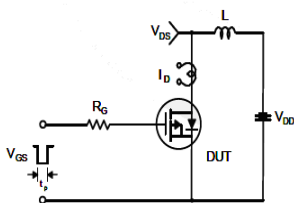


Fig10. Unclamped Inductive Test Circuit and Waveforms

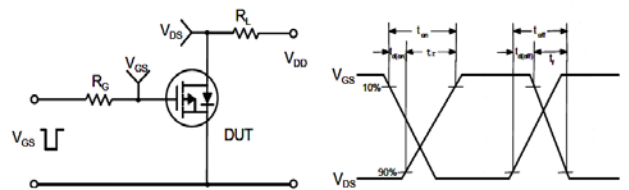
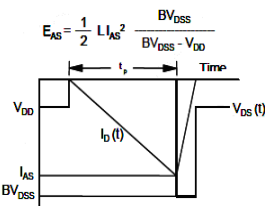
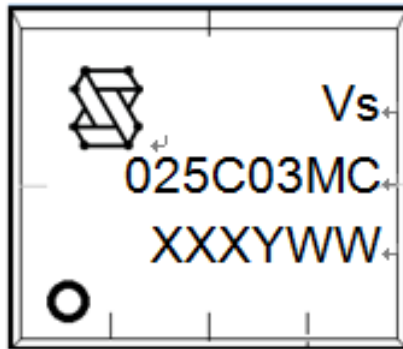


Fig11. Switching Time Test Circuit and waveforms

Marking Information



1st line: Company Code (Vs), Company Logo

2nd line: Part Number (025C03MC)

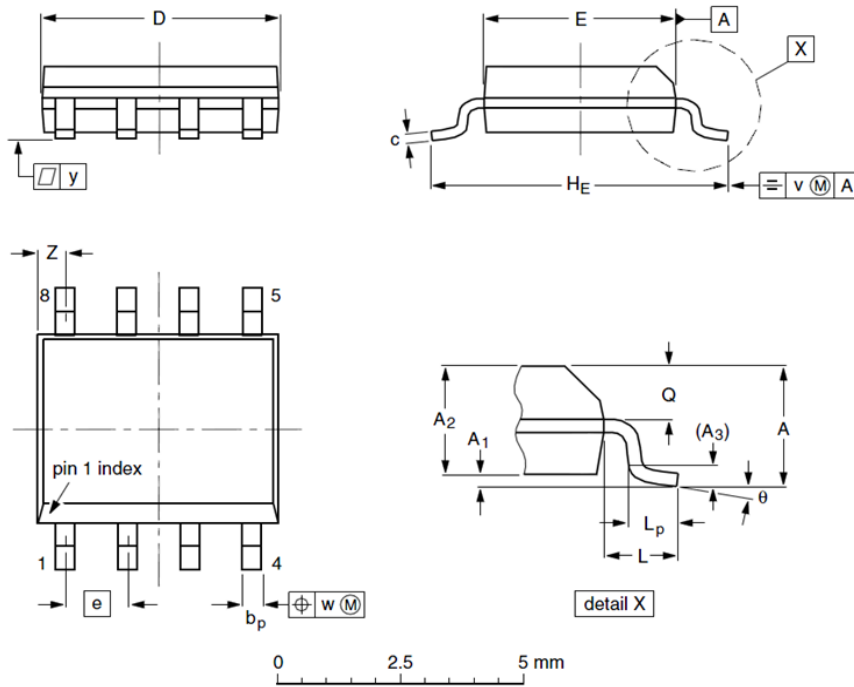
3rd line: Date code (XXXYWW)

LOT: Wafer Lot Number

Y: Year Code, e.g. E means 2017

WW: Week Code

SOP8 Package Outline Data



Label	Dimensions (unit: mm)		
	Min	Typ	Max
A	--	--	1.75
A ₁	0.10	0.18	0.25
A ₂	1.25	1.35	1.50
A ₃	--	0.25	--
b _p	0.36	0.42	0.51
c	0.19	0.22	0.25
D	4.80	4.92	5.00
E	3.80	3.90	4.00
e	--	1.27	--
H _E	5.80	6.00	6.20
L	--	1.05	--
L _p	0.40	0.68	1.00
Q	0.60	0.65	0.725
v	--	0.25	--
w	--	0.25	--
y	--	0.10	--
Z	0.30	0.50	0.70
θ	0°		8°

Notes:

1. Follow JEDEC MS-012.
2. Dimension "D" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15mm per side.
3. Dimension "E" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.25mm per side.
4. Dimension "b_p" does NOT include dambar protrusion. Allowable dambar protrusion shall be 0.1mm total in excess of "b_p" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot.

Customer Service

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